

## Silicon Power Schottky Diode

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 300\text{ A}$

### Features

- High Surge Capability
- Types up to 100 V  $V_{RRM}$

Twin Tower Package



Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR30045CT (R)	MBR30060CT (R)	MBR30080CT (R)	MBR300100CT (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		45	60	80	100	V
RMS reverse voltage	$V_{RMS}$		32	42	56	70	V
DC blocking voltage	$V_{DC}$		45	60	80	100	V
Continuous forward current	$I_F$	$T_C \leq 140\text{ °C}$	300	300	300	300	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	2500	2500	2500	2500	A
Operating temperature	$T_j$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MBR30045CT (R)	MBR30060CT (R)	MBR30080CT (R)	MBR300100CT (R)	Unit
Diode forward voltage	$V_F$	$I_F = 150\text{ A}$ , $T_j = 25\text{ °C}$	0.65	0.75	0.84	0.84	V
Reverse current	$I_R$	$V_R = 20\text{ V}$ , $T_j = 25\text{ °C}$	8	8	8	8	mA
		$V_R = 20\text{ V}$ , $T_j = 125\text{ °C}$	200	200	200	200	

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.4	0.4	0.4	0.4	°C/W
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Figure .1-Typical Forward Characteristics

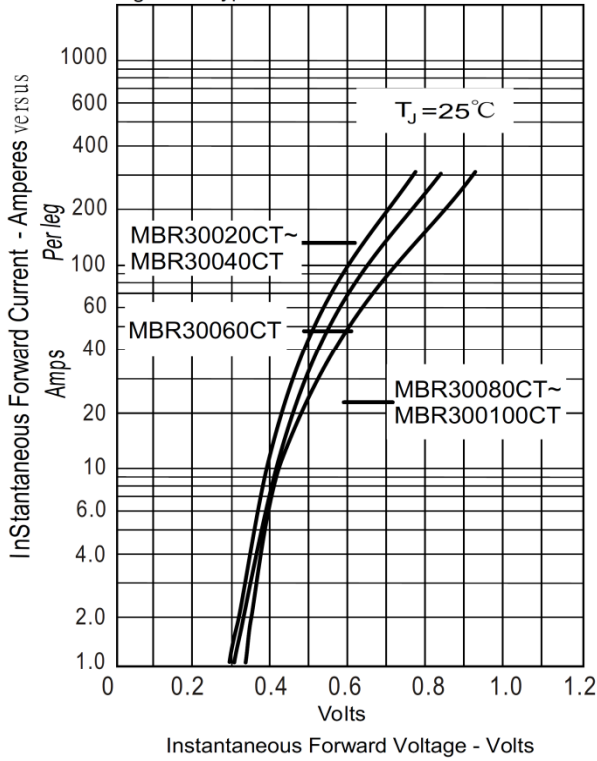


Figure .2-Forward Derating Curve

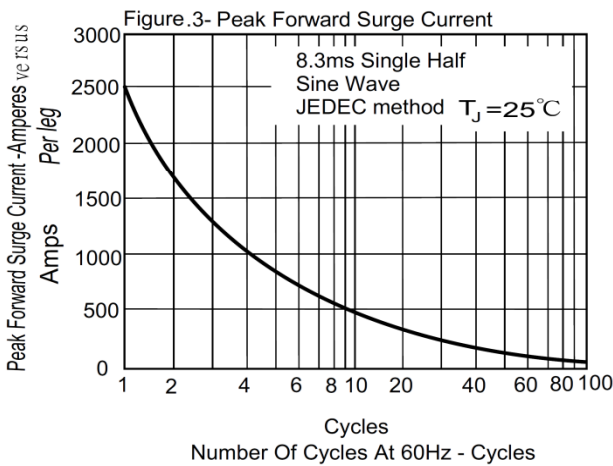
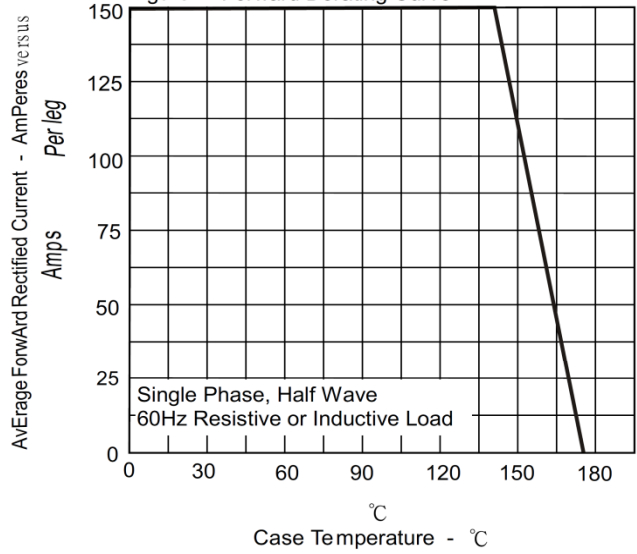


Figure .4-Typical Reverse Characteristics

